

**AMENDMENTS TO THE CLAIMS**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Currently Amended)      A semiconductor device comprising:  
a semiconductor substrate formed with pads;  
a passivation film formed on a surface of said semiconductor substrate on a pad forming side; and  
lands for connection to external terminals, said lands being formed on an insulating film formed on a surface of said passivation film opposite to said semiconductor substrate,  
wherein:  
said pads and said lands are connected by conductive wiring lines; ~~and~~  
said external terminals are solder bumps and said lands are formed of a material comprising Cu; and  
projections, made of a material comprising Cu, are formed on each of said lands at positions where said lands are connected to the external terminals.

2. (Currently Amended)      A semiconductor device comprising:  
a silicon substrate formed with pads;  
a passivation film formed on a surface of said silicon substrate on a pad forming side;  
lands for connection to external terminals which are solder bumps, said lands being made of a material comprised of Cu and formed on the surface of said silicon substrate on the pad forming side, respectively; and

wiring lines connecting said pads and said lands,  
wherein:  
an insulating film is formed between said passivation film and said lands;  
projections, made of a material comprising Cu, are formed on said lands on a  
surface opposite to said silicon substrate; and  
said projections are connected to the external terminals, respectively.

3. (Withdrawn) A semiconductor device comprising:  
a semiconductor substrate formed with pads;  
a passivation film formed on a surface of said semiconductor substrate on a  
pad forming side;  
lands for connection to external terminals, said lands being formed on the  
surface of said semiconductor substrate on the pad forming side; and  
wiring lines connecting said pads and said lands,  
wherein said wiring lines each include a first wiring line connected to one of  
said pads and a second wiring line connected to one of said lands.

4. (Withdrawn) A semiconductor device comprising:  
a silicon substrate formed with pads;  
a passivation film formed on a surface of said silicon substrate on a pad  
forming side;  
lands for connection to external terminals, said lands being formed on the  
surface of said silicon substrate on the pad forming side; and  
wiring lines connecting said pads and said lands,  
wherein:  
said wiring line each include a first wiring line connected to one of said pads  
and a second wiring line connected to one of said lands;

an insulating film is formed between said passivation film and said lands;  
~~projection~~ projections are formed on said lands, respectively, on a surface  
opposite to said silicon substrate; and  
said projections are connected to the external terminals.

5. (Currently Amended) A semiconductor device comprising:  
a semiconductor substrate formed with pads;  
a passivation film formed on a surface of said semiconductor substrate on a  
pad forming side;

lands for connection to external terminals, said lands being formed on the  
surface of said semiconductor substrate on the pad forming side,

wherein said external terminals are solder bumps and said lands are formed  
of a material comprising Cu;

the external terminals being connected to said lands,

wherein said projections, made of a material comprising Cu, are formed on  
said lands at positions where said lands are connected to the external terminals,  
respectively; and

wiring lines connecting said pads and said lands,

wherein an insulating protective film is formed on the surface of said  
semiconductor substrate on the pad forming side in an area other than the external  
terminals.

6. (Withdrawn) A semiconductor device comprising:  
a semiconductor substrate formed with pads;  
a passivation film formed on a surface of said semiconductor substrate on a  
pad forming side;

conductive wiring lines connected to the pads on said semiconductor substrate;

lands connected to said conductive wiring lines;

projections formed on said lands;

external terminals connected to said projections;

a first protective film formed between said semiconductor substrate and said lands and being in contact with said lands; and

a second protective film having an exposed surface on an external terminal forming side.

7. (Withdrawn) A semiconductor device comprising:

a silicon substrate formed with pads;

a passivation film formed on a surface of said silicon substrate on a pad forming side;

lands for connection to external terminals, said lands being formed on the surface of said silicon substrate on the pad forming side; and

wiring lines connecting said pads and said lands,

wherein:

each of said wiring lines includes a first wiring line connected to one of said pads and a second wiring line connected to one of said lands;

a first region formed with a first insulating film is formed between said passivation film and said lands;

a second insulating film is formed between said passivation film and said lands, and wherein projections are formed on said lands on a surface opposite to said silicon substrate, and the projections are connected to the external terminals.

8. (Withdrawn) A semiconductor device according to claim 6, wherein the second protective film is made of material having an elastic modulus lower than the first protective film.

9. (Withdrawn) A semiconductor device according to any one of claims ~~1, 2, 4, 6, 7 and 8~~ 4, 6, 7 and 8, wherein the projections are positioned in projected areas of said lands.

10. (Withdrawn) A semiconductor device according to any one of claims ~~1, 2, 4, 6, 7 and 8~~ 4, 6, 7 and 8, wherein the external terminals and the projections are respectively each bonded via a metal thin film formed on a surface of the projection.

11. (Previously Presented) A semiconductor device according to any one of claims 1 to 10, wherein in a semiconductor module having the semiconductor device mounted on a printed circuit board via the external terminals, a bonding area between a bonding pad of the printed circuit board and one of the external terminals is set larger than a bonding area between one of the projections and said one of the external terminals in a direction of disposing the external terminals.

12. (Previously Presented) A semiconductor device according to any one of claims 1 to 10, wherein in a semiconductor module having the semiconductor device mounted on a printed circuit board via the external terminals, an area near a bonding area between a bonding pad of the printed circuit board and one of the external terminals is covered with resin.

13. (Previously Presented) A semiconductor device according to claim 1 or 2, wherein said projections each include a first portion which extends into a corresponding one of said external terminals and a second portions located between a corresponding one of said lands and said first portion.

14. (Previously Presented) A semiconductor device according to claim 13, wherein each of said first portions of said projections has substantially the same width as a corresponding one of said second portions of said projections.

15. (Withdrawn) A semiconductor device according to claim 13, wherein each of said first portions is wider than a corresponding one of said second portions.

16. (Withdrawn) A semiconductor device according to claim 15, wherein said insulating film extends into an area between said wider first portions and said corresponding lands.

17. (New) A semiconductor device according to claim 1, wherein the projections are positioned in projected areas of said lands.

18. (New) A semiconductor device according to claim 2, wherein the projections are positioned in projected areas of said lands.

19. (New) A semiconductor device according to claim 1, wherein the external terminals and the projections are respectively each bonded via a metal thin film formed on a surface of the projection.

20. (New) A semiconductor device according to claim 2, wherein the external terminals and the projections are respectively each bonded via a metal thin film formed on a surface of the projection.

21. (New) A semiconductor device according to claim 1,  
wherein a protective film having an opening in a region in which said land is disposed is formed on said conductive wiring and a portion of said projection is projected from a surface of said protective film.